

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A semiconductor device comprising:

a first interlayer insulating layer;

a trench formed in the first interlayer insulating layer;

a barrier layer formed in the trench;

a conductive layer ~~buried in~~ formed within the barrier layer in the trench, the conductive layer having a surface thereof higher than a highest surface of the first interlayer insulating layer surrounding and adjoining the trench;

an insulating film having a flat surface and covering the first interlayer insulating layer and the conductive layer, the insulating film configured to prevent diffusion of a conductor material in the conductive layer; and

a second interlayer insulating layer formed on the insulating film, the second interlayer insulating layer having a high etching selective ratio to the insulating film.

Claim 2 (Original): The semiconductor device according to claim 1, wherein a film thickness of the insulating film on the first interlayer insulating layer is greater than that on the conductive layer.

Claim 3 (Original): The semiconductor device according to claim 1, wherein the insulating film is made of a coating type material.

Claim 4 (Canceled).

Claim 5 (Original): The semiconductor device according to claim 1, wherein at least any one of the first interlayer insulating layer and the second interlayer insulating layer is made of an insulating material having a relative dielectric constant lower than that of an SiO<sub>2</sub> film.

Claim 6 (Original): The semiconductor device according to claim 1, wherein the insulating film is made of an insulating material having a relative dielectric constant lower than that of an SiO<sub>2</sub> film.

Claim 7 (Canceled).

Claim 8 (Original): The semiconductor device according to claim 1, wherein the conductive layer includes a Cu wiring layer.

Claim 9 (Original): The semiconductor device according to claim 1, wherein at least any one of the first interlayer insulating layer and the second interlayer insulating layer is made of methylpolysiloxane.

Claim 10 (Previously Presented): The semiconductor device according to claim 1, wherein the insulating film is made of any one of polyarylene and benzo cyclo-butene.

Claims 11-30 (Canceled)

Claim 31 (Previously Presented): The semiconductor device according to claim 1, wherein the insulating film suppresses a progress of etching of a contact hole formed in the second interlayer insulating layer so as not to reach the first interlayer insulating layer.